January 2005

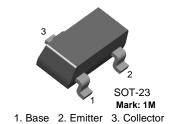
MMBTA13 NPN Darlington Transistor



SEMICONDUCTOR®

MMBTA13 NPN Darlington Transistor

- This device is designed for applications requiring extremely high Current gain at collector Currents to 1.0A.
- Sourced from process 05.
- See MPSA14 for characteristics.



Absolute Maximum Ratings T_a = 25°C unless otherwise noted

| Symbol | Parameter | Value | Units |
|-----------------------------------|--|--|-------|
| V _{CES} | Collector-Emitter Voltage | 30 | V |
| V _{CBO} | Collector-Base Voltage 30 | | V |
| V _{EBO} | Emitter-Base Voltage | 10 | V |
| I _C | Collector Current - Continuous | 1.2 | A |
| T _J , T _{STG} | Operating and Storage Junction Temperature Range | rage Junction Temperature Range -55 to +150 °C | |

Electrical Characteristics T_a=25°C unless otherwise noted

| Symbol | Parameter | Test Condition | Min. | Max. | Units |
|-----------------------|--------------------------------------|--|-----------------|------|-------|
| Off Charac | teristics | | | | |
| V _{(BR)CES} | Collector-Emitter Breakdown Voltage | $I_{\rm C} = 100 \mu {\rm A}, I_{\rm B} = 0$ | 30 | | V |
| I _{CBO} | Collector-Cutoff Current | $V_{CB} = 30V, I_E = 0$ | | 100 | nA |
| I _{EBO} | Emitter-Cutoff Current | $V_{EB} = 10V, I_{C} = 0$ | | 100 | nA |
| On Charac | teristics * | | | | |
| h _{FE} | DC Current Gain | $V_{CE} = 5.0V, I_C = 10mA$ $V_{CE} = 5.0, I_C = 100mA$ | 5,000 10,000 | | |
| V _{CE (sat)} | Collector-Emitter Saturation Voltage | I _C = 100mA, I _B = 0.1mA | | 1.5 | V |
| V _{BE (on)} | Base-Emitter On Voltage | I _C = 100mA,V _{CE} = 5.0V | | 2.0 | V |
| Small Sign | al Characteristics | | | | |
| f _T | Current Gain Bandwidth Product | I _C = 10mA, V _{CE} = 10V, f = 100MHz | 125 | | pF |

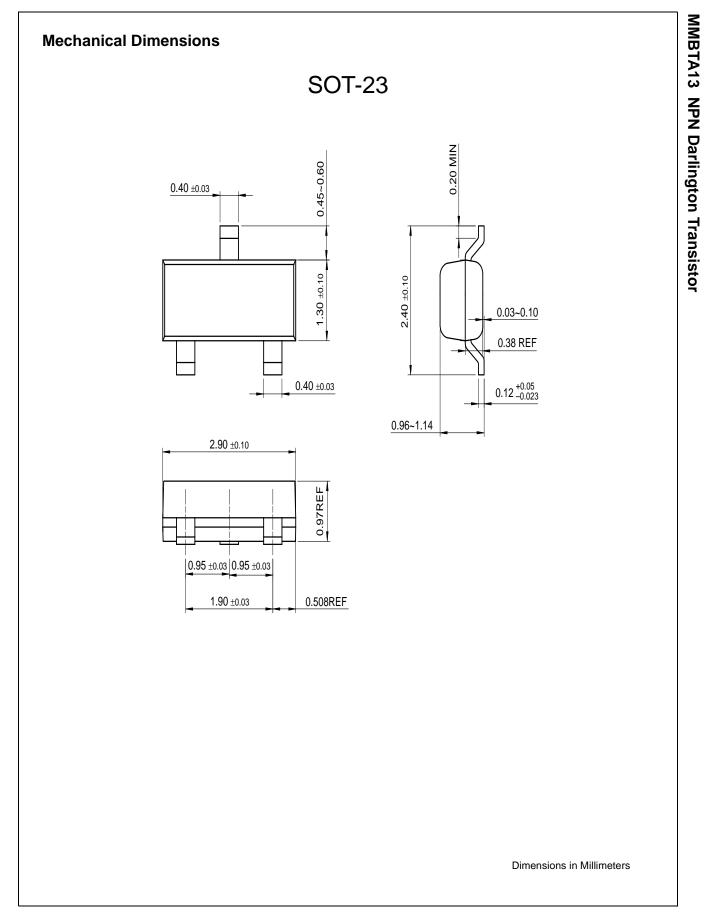
* Pulse Test: Pulse Width≤300µs, Duty Cycle≤2%

| MMBTA13 |
|------------|
| NPN |
| Darlington |
| Transistor |

Thermal Characteristics ${\tt T}_a{=}25^\circ{\tt C}$ unless otherwise noted

| Symbol | Parameter | Max. | Units |
|-----------------------|---|------------|-------------|
| P _D | Total Device Dissipation Derate above 25°C | 350 2.8 | mW mW/°C |
| $R_{	extsf{	heta}JC}$ | Thermal Resistance, Junction to Case | | °C/W |
| R_{\thetaJA} | Thermal Resistance, Junction to Ambient | 357 | °C/W |

* Device mounted on FR-4PCB 1.6" \times 1.6" \times 0.06".



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|--------------------------|---------------------------|---|
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